



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C
20V	$3.0\Omega @ V_{GS} = 4.5V$	240mA
	6.0Ω @ V _{GS} = 1.8V	170mA

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- **Power Management Functions**

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.05V Max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package, 0.4mm Maximum Package
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

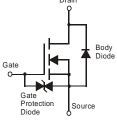
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (Approximate)



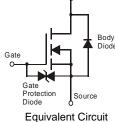




Bottom View



Top View



Ordering Information (Note 4)

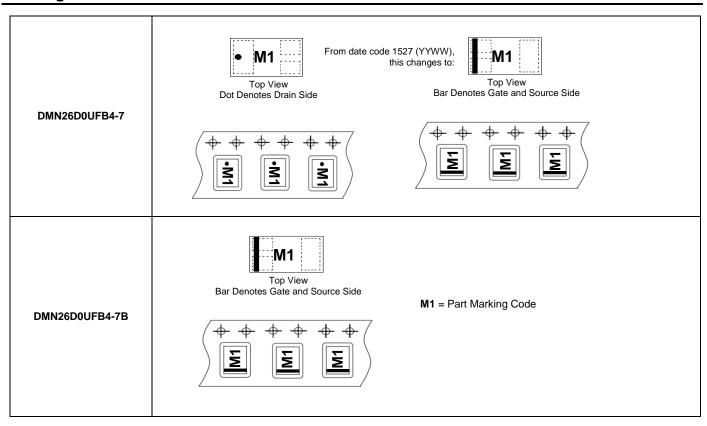
Part Number	Case	Packaging
DMN26D0UFB4-7	X2-DFN1006-3	3,000/Tape & Reel
DMN26D0UFB4-7B	X2-DFN1006-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	240 190	mA
Continuous Drain Current (Note 5) $V_{GS} = 1.8V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$		I _D	180 140	mA	
Pulsed Drain Current - T _P = 10µs	I _{DM}	805	mA		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Total Power Dissipation (Note 5) @T _A = +25°C	P_{D}	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	357	°C/W
Operating and Storage Temperature Range	T_J, T_STG	-55 to +150	°C

Note: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

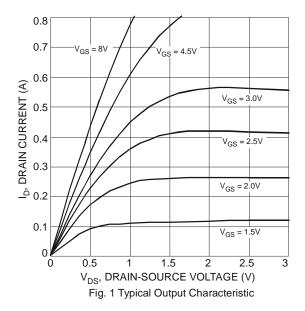


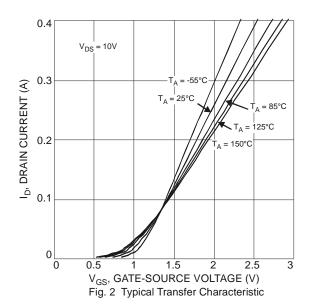
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)	OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 100\mu A$	
Zero Gate Voltage Drain Current @ T _C = +25°C	I _{DSS}	_	_	500	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	±1 ±100	μA nA	$V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)			•	•			
Gate Threshold Voltage	V _{GS(th)}	0.45	_	1.05	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_ _ _	1.8 2.5 3.4 4.7	3.0 4.0 6.0 10.0	Ω	$V_{GS} = 4.5V, I_D = 100mA$ $V_{GS} = 2.5V, I_D = 50mA$ $V_{GS} = 1.8V, I_D = 20mA$ $V_{GS} = 1.5V, I_D = 10mA$	
Forward Transconductance	Y _{fs}	180	242	_	mS	$V_{DS} = 10V, I_D = 0.1A$	
Source-Drain Diode Forward Voltage	V_{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 7)						_	
Input Capacitance	C _{iss}	_	14.1	28.2	pF		
Output Capacitance	Coss	_	2.9	5.8	pF	$V_{DS} = 15V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	1.6	3.2	pF	1 - 1.01/11/2	
SWITCHING CHARACTERISTICS (Note 7)							
Turn-On Delay Time	t _{d(on)}	_	3.8	_			
Rise Time	t _r	_	7.9	_	ns	$V_{GS} = 4.5V, V_{DD} = 10V$	
Turn-Off Delay Time	t _{d(off)}		13.4	_	115	$I_D=200mA,\ R_G=2.0\Omega$	
Fall Time	t _f	_	15.2	_			

Notes:

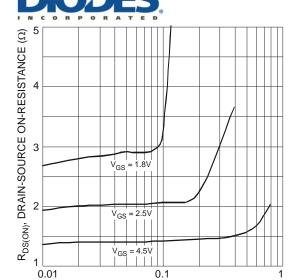
^{7.} Guaranteed by design. Not subject to product testing.

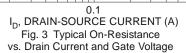




^{6.} Short duration pulse test used to minimize self-heating effect.

DMN26D0UFB4





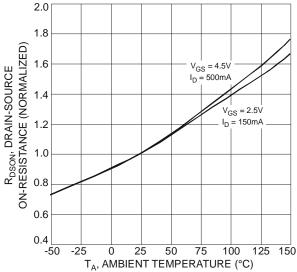


Fig. 5 On-Resistance Variation with Temperature

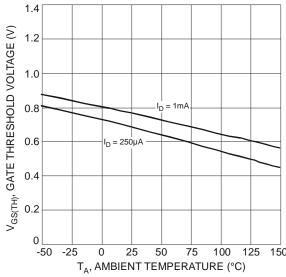


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

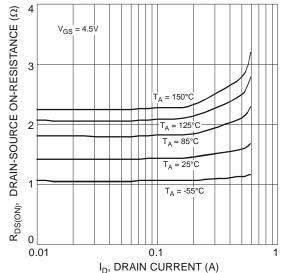


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

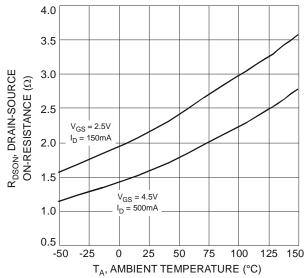


Fig. 6 On-Resistance Variation with Temperature

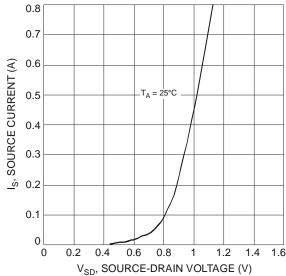
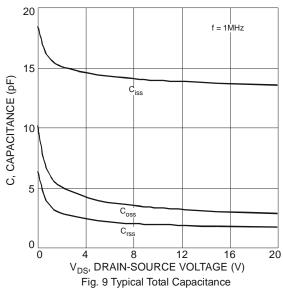


Fig. 8 Diode Forward Voltage vs. Current







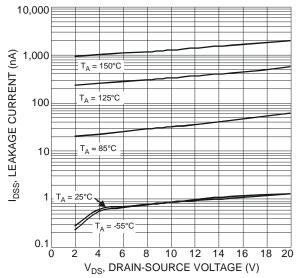


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

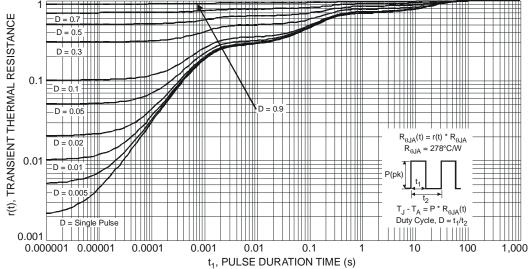
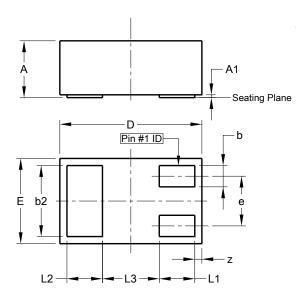


Fig. 11 Transient Thermal Response



Package Outline Dimensions

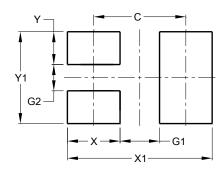
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1006-3				
Dim	Min	Max	Тур	
Α		0.40	_	
A1	0.00	0.05	0.03	
b	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.05	1.00	
Е	0.55	0.65	0.60	
е	1	ı	0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3	-	-	0.40	
Z	0.02	0.08	0.05	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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